

SMAF Plastic-Encapsulate Diodes

SS52F THRU SS520F Schottky Rectifier Diodes

Features

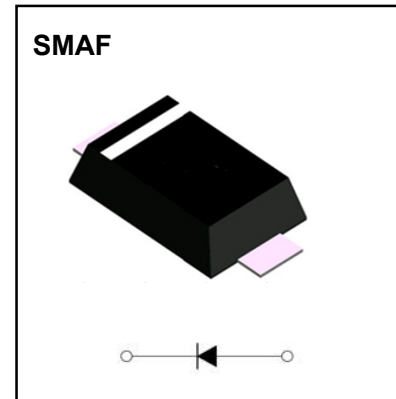
- $I_{F(AV)}$ 5A
- V_{RRM} 20V-200V
- High surge current capability
- Polarity: Color band denotes cathode

Applications

- Rectifier

Marking

- SS5X
X : From 2 To 20



Limiting Values(Absolute Maximum Rating)

Item	Symbol	Unit	Test Conditions	SS5													
				2F	3F	4F	5F	6F	8F	10F	15F	20F					
Repetitive Peak Reverse Voltage	V_{RRM}	V		20	30	40	50	60	80	100	150	200					
Maximum RMS Voltage	V_{RMS}	V		14	21	28	35	42	56	70	105	140					
Average Forward Current	$I_{F(AV)}$	A	60Hz Half-sine wave, Resistance load	5.0													
Surge(Non-repetitive)Forward Current	I_{FSM}	A	60Hz Half-sine wave, 1 cycle, $T_a=25^\circ\text{C}$	150													
Junction Temperature	T_J	$^\circ\text{C}$		-55 ~ +150													
Storage Temperature	T_{STG}	$^\circ\text{C}$		-55 ~ +150													

Electrical Characteristics ($T = 25^\circ\text{C}$ Unless otherwise specified)

Item	Symbol	Unit	Test Condition	SS5											
				2F	3F	4F	5F	6F	8F	10F	15F	20F			
Peak Forward Voltage	V_F	V	$I_F=5.0\text{A}$	0.55		0.70		0.85		0.95					
Peak Reverse Current	I_{RRM1}	mA	$V_{RM}=V_{RRM}$	$T_a=25^\circ\text{C}$		0.5		0.1							
	I_{RRM2}			$T_a=100^\circ\text{C}$		10		5.0							
Thermal Resistance(Typical)	$R_{\theta J-A}$	$^\circ\text{C}/\text{W}$	Between junction and ambient		114										
	$R_{\theta J-L}$		Between junction and terminal		12										
Juction Capacitance (Typical)	C_j	pF	Measured at 1MHZ and Applied Reverse Voltage of 4.0 V.D.C		260		220		130		100		80		

Notes:

Thermal resistance from junction to ambient and from junction to lead mounted on FR4 PCB double sided copper mini pad

Typical Characteristics

FIG.1: FORWARD CURRENT DERATING CURVE

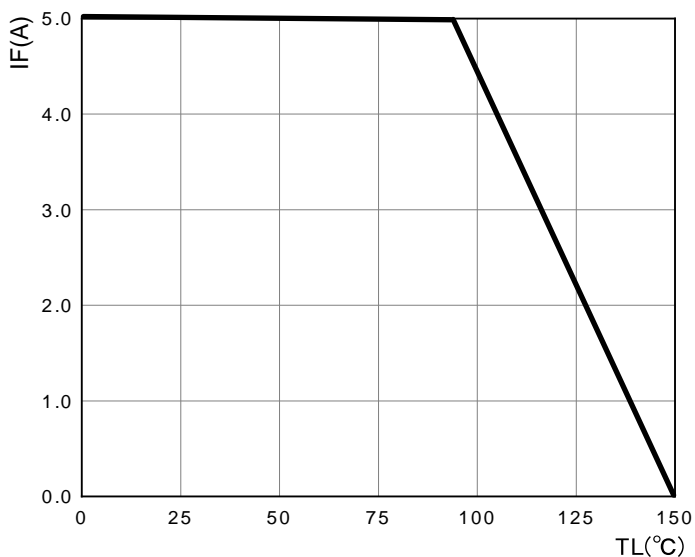
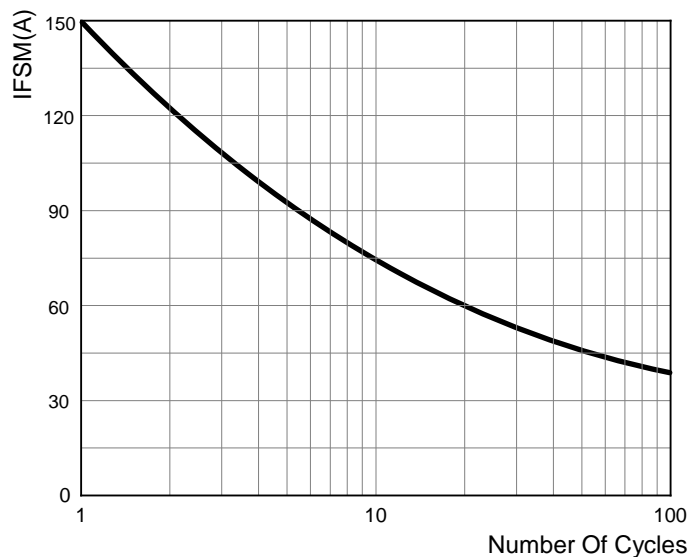
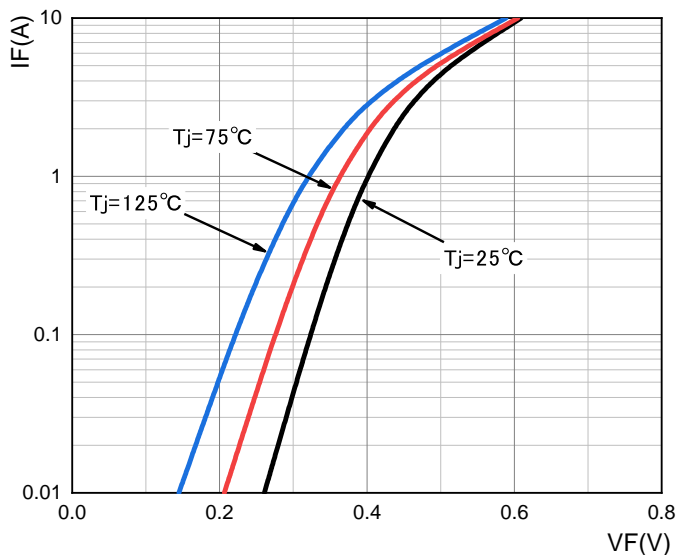


FIG.2: MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT



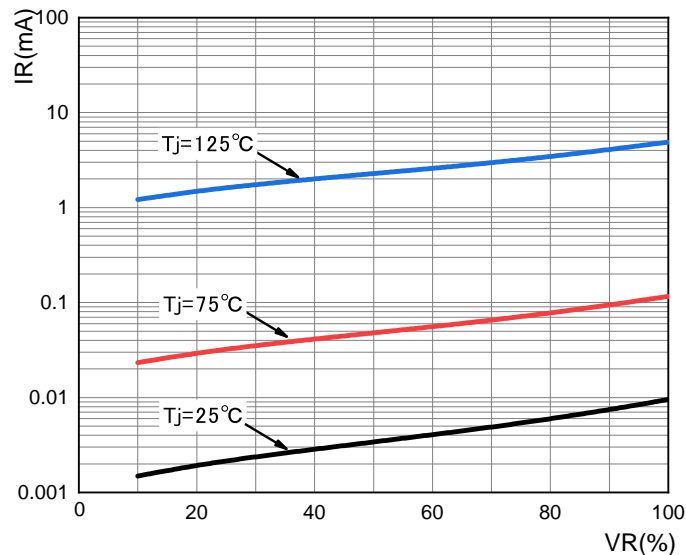
SS52F-SS54F

FIG.3: TYPICAL FORWARD CHARACTERISTICS



SS52F-SS54F

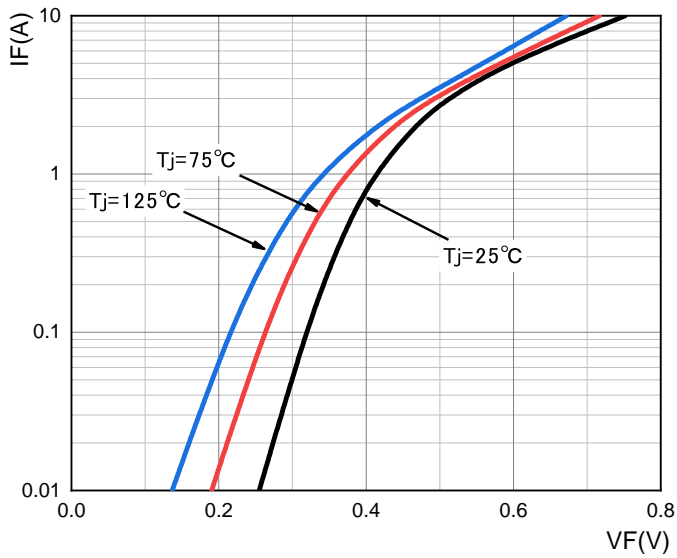
FIG.4: TYPICAL REVERSE CHARACTERISTICS



Typical Characteristics

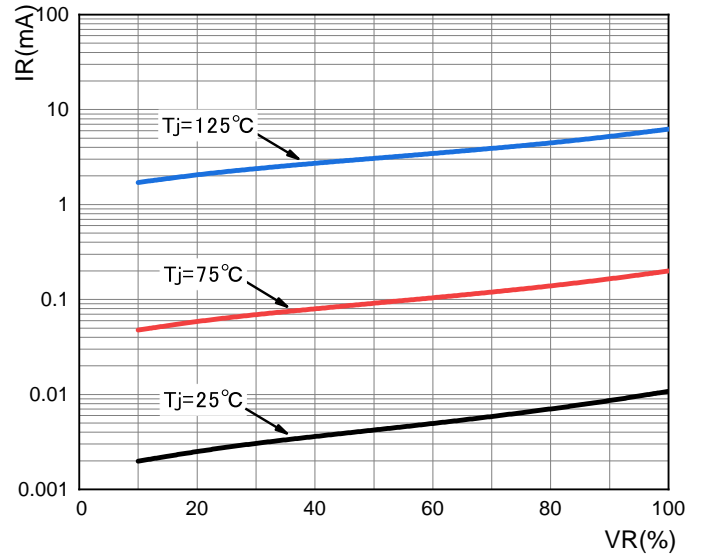
SS55F-SS56F

FIG.5: TYPICAL FORWARD CHARACTERISTICS



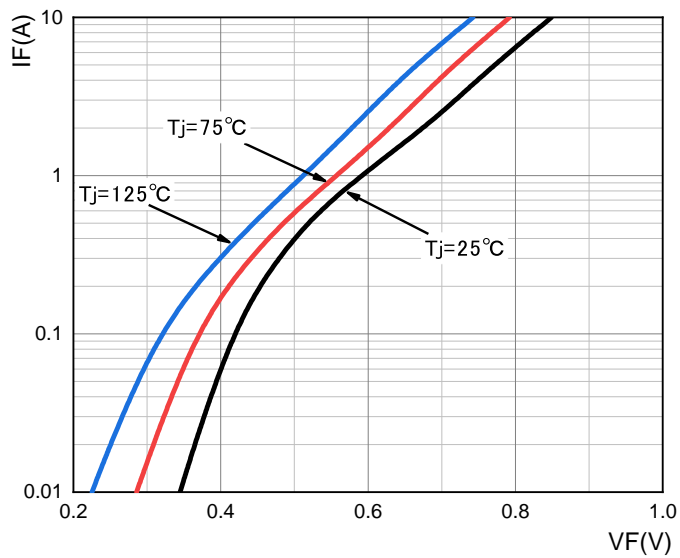
SS55F-SS56F

FIG.6: TYPICAL REVERSE CHARACTERISTICS



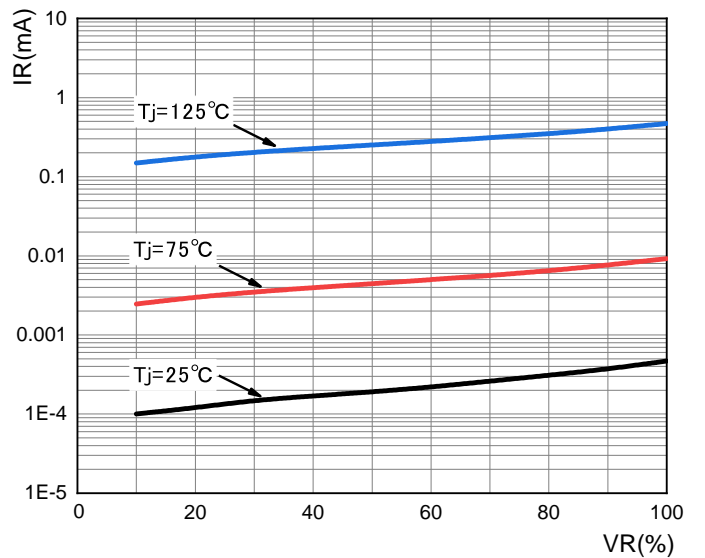
SS58F-SS510F

FIG.7: TYPICAL FORWARD CHARACTERISTICS



SS58F-SS510F

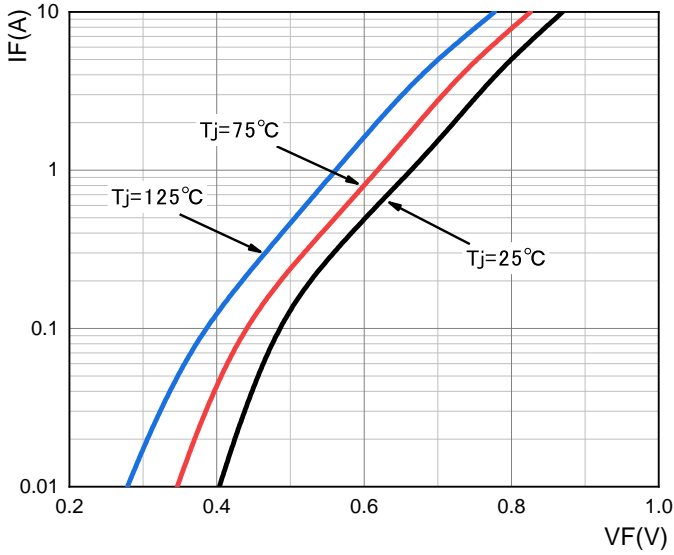
FIG.8: TYPICAL REVERSE CHARACTERISTICS



Typical Characteristics

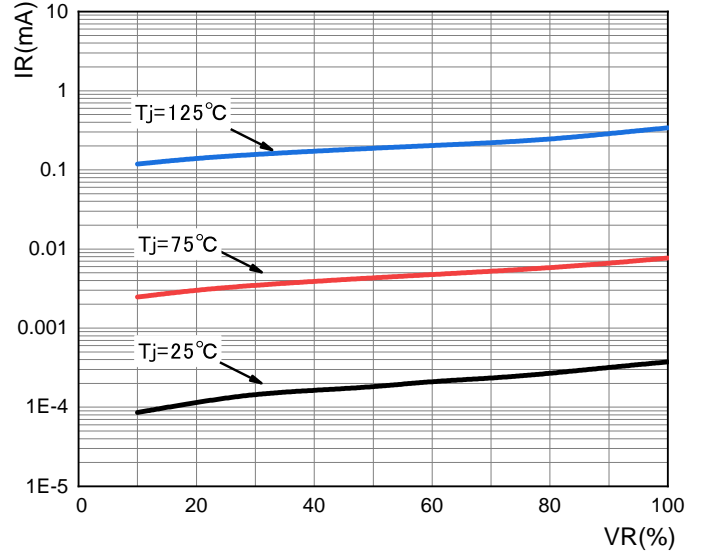
SS515F

FIG.9: TYPICAL FORWARD CHARACTERISTICS



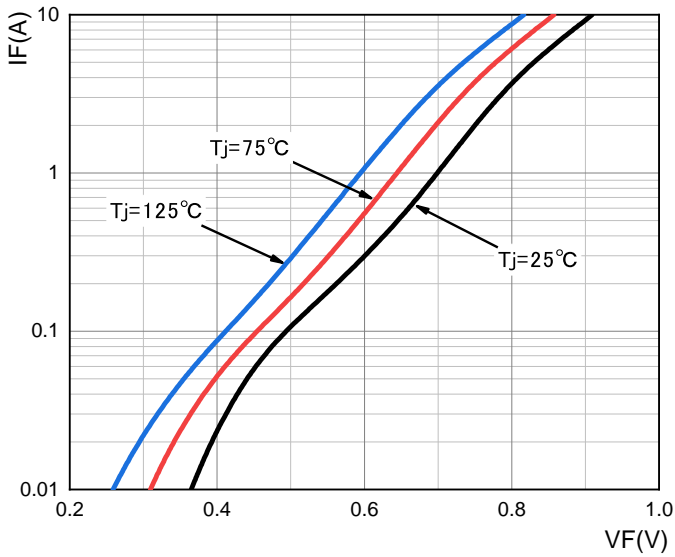
SS515F

FIG.10: TYPICAL REVERSE CHARACTERISTICS



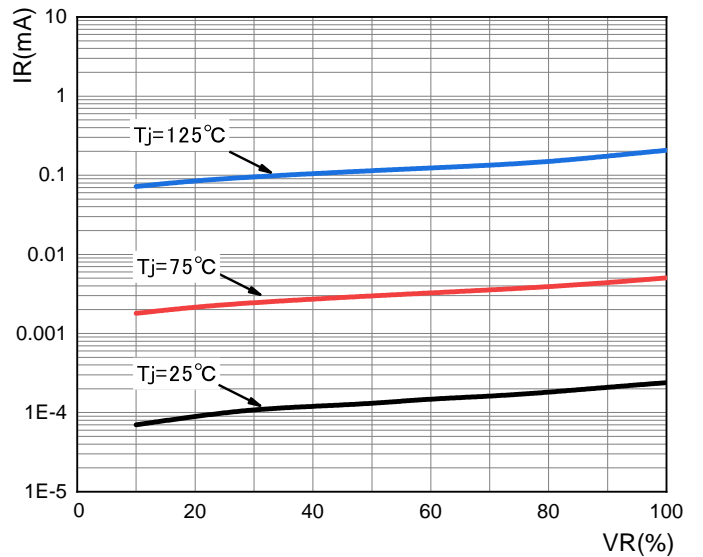
SS520F

FIG.11: TYPICAL FORWARD CHARACTERISTICS

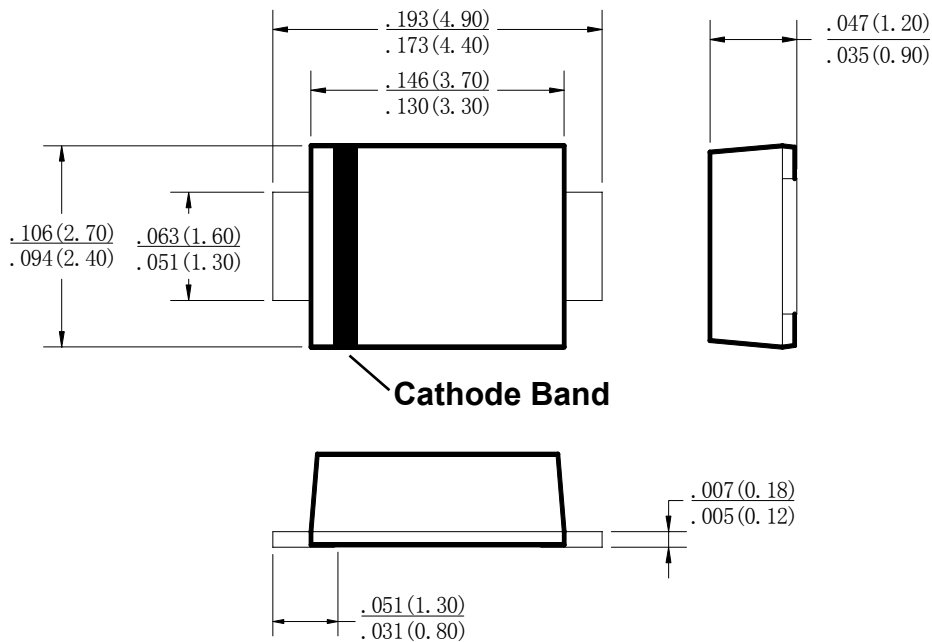


SS520F

FIG.12: TYPICAL REVERSE CHARACTERISTICS



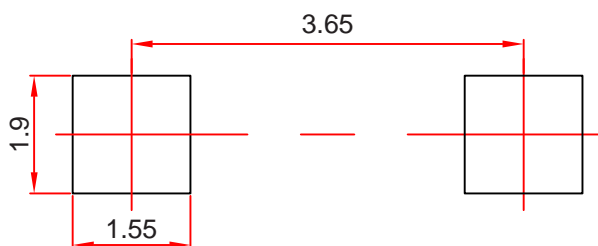
SMAF Package Outline Dimensions



Cathode Band

Dimensions in inches and (millimeters)

SMAF Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05 mm.
3. The pad layout is for reference purposes only.

NOTICE

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Reel Taping Specifications For Surface Mount Devices- SMAF

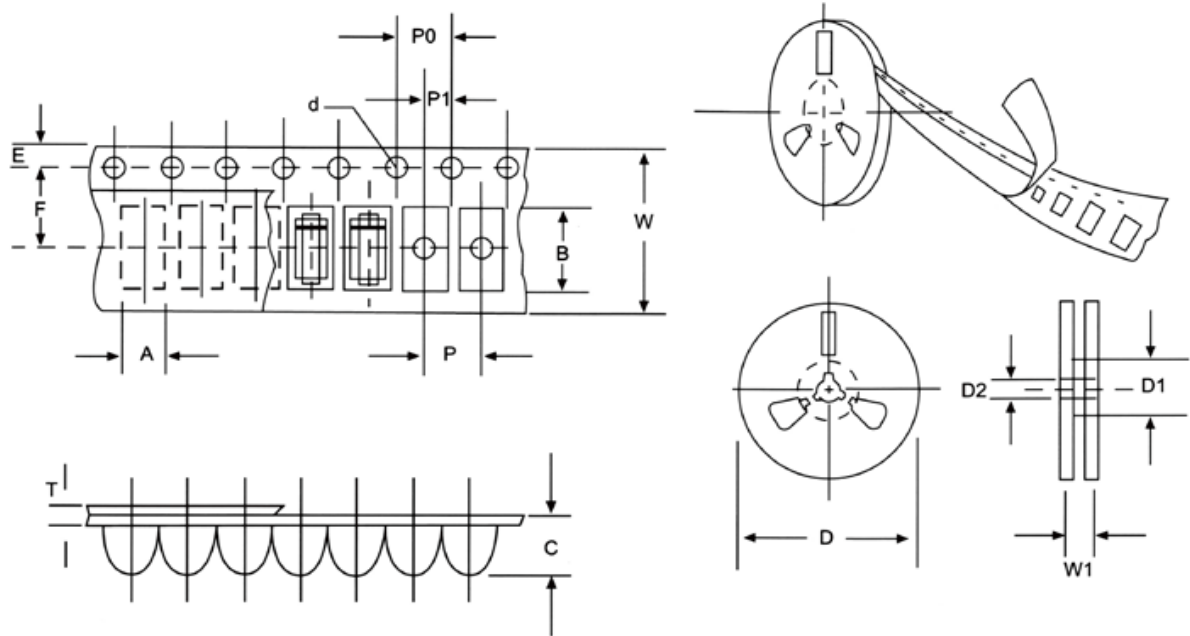


FIG: CONFIGURATION OF SURFACE MOUNTED DEVICES TAPING

ITEM	SYMBOL	SMAF mm(inch)
Carrier width	A	2.83±0.1(0.112±0.004)
Carrier length	B	4.90±0.1(0.193±0.004)
Carrier depth	C	1.45±0.1(0.057±0.004)
Sprocket hole	d	1.55±0.05(0.061±0.002)
Reel outside diameter	D	178±2.0(7.0±0.079)
Reel inner diameter	D1	54±1.0(2.13±0.039)
Feed hole diameter	D2	13±0.5(0.512±0.020)
Sprocket hole position	E	1.75±0.1(0.069±0.004)
Punch hole position	F	5.5±0.05(0.217±0.002)
Punch hole pitch	P	4.0±0.1(0.157±0.004)
Sprocket hole pitch	P0	4.0±0.1(0.157±0.004)
Embossment center	P1	2.0±0.1(0.079±0.004)
Total tape thickness	T	0.23-0.29(0.009-0.011)
Tape width	W	12.0±0.1(0.472±0.004)
Reel width	W1	16.8±2.0(0.661±0.079)

NOTE: Devices are packed in accordance with EIA standard RS-481-A and specification given above.